

MC54/74HC393

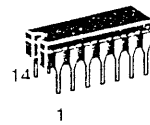
Dual 4-Stage Binary Ripple Counter High-Performance Silicon-Gate CMOS

The MC54/74HC393 is identical in pinout to the LS393. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

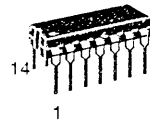
This device consists of two independent 4-bit binary ripple counters with parallel outputs from each counter stage. A ± 256 counter can be obtained by cascading the two binary counters.

Internal flip-flops are triggered by high-to-low transitions of the clock input. Reset for the counters is asynchronous and active-high. State changes of the Q outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and should not be used as clocks or as strobes except when gated with the Clock of the HC393.

- Output Drive Capability: 10 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 2 to 6 V
- Low Input Current: 1 μ A
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance with the Requirements Defined by JEDEC Standard No. 7A
- Chip Complexity: 236 FETs or 59 Equivalent Gates



J SUFFIX
CERAMIC PACKAGE
CASE 632-08



N SUFFIX
PLASTIC PACKAGE
CASE 646-06

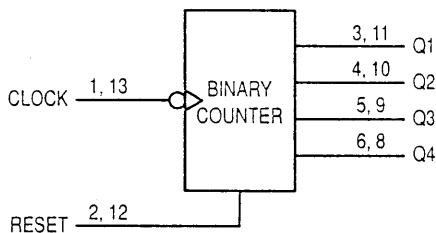


D SUFFIX
SOIC PACKAGE
CASE 751A-03

ORDERING INFORMATION

MC54HCXXXJ	Ceramic
MC74HCXXXN	Plastic
MC74HCXXXD	SOIC

LOGIC DIAGRAM



PIN 14 = V_{CC}
PIN 7 = GND

PIN ASSIGNMENT

CLOCK a	1	14	V_{CC}
RESET a	2	13	CLOCK b
Q1 _a	3	12	RESET b
Q2 _a	4	11	Q1 _b
Q3 _a	5	10	Q2 _b
Q4 _a	6	9	Q3 _b
GND	7	8	Q4 _b

FUNCTION TABLE

Inputs		Outputs
Clock	Reset	
X	H	L
H	L	No Change
L	L	No Change
	L	No Change
	L	Advance to Next State



MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V_{in}	DC Input Voltage (Referenced to GND)	- 1.5 to $V_{CC} + 1.5$	V
V_{out}	DC Output Voltage (Referenced to GND)	- 0.5 to $V_{CC} + 0.5$	V
I_{in}	DC Input Current, per Pin	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package†	750 500	mW
T_{stg}	Storage Temperature	- 65 to + 150	°C
T_L	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic or SOIC DIP) (Ceramic DIP)	260 300	°C

* Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

† Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

Ceramic DIP: - 10 mW/°C from 100° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2.

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage (Referenced to GND)	2.0	6.0	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	- 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time (Figure 1)			ns
	$V_{CC} = 2.0 \text{ V}$	0	1000	
	$V_{CC} = 4.5 \text{ V}$	0	500	
	$V_{CC} = 6.0 \text{ V}$	0	400	

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

Symbol	Parameter	Test Conditions	V_{CC} V	Guaranteed Limit			Unit
				- 55 to 25°C	$\leq 85^\circ\text{C}$	$\leq 125^\circ\text{C}$	
V_{IH}	Minimum High-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ or $V_{CC} - 0.1 \text{ V}$ $ I_{out} \leq 20 \mu\text{A}$	2.0	1.5	1.5	1.5	V
			4.5	3.15	3.15	3.15	
			6.0	4.2	4.2	4.2	
V_{IL}	Maximum Low-Level Input Voltage	$V_{out} = 0.1 \text{ V}$ or $V_{CC} - 0.1 \text{ V}$ $ I_{out} \leq 20 \mu\text{A}$	2.0	0.3	0.3	0.3	V
			4.5	0.9	0.9	0.9	
			6.0	1.2	1.2	1.2	
V_{OH}	Minimum High-Level Output Voltage	$V_{in} = V_{IH}$ or V_{IL} $ I_{out} \leq 20 \mu\text{A}$	2.0	1.9	1.9	1.9	V
			4.5	4.4	4.4	4.4	
			6.0	5.9	5.9	5.9	
			$V_{in} = V_{IH}$ or V_{IL} $ I_{out} \leq 4.0 \text{ mA}$ $ I_{out} \leq 5.2 \text{ mA}$	4.5	3.98	3.84	
			6.0	5.48	5.34	5.20	
V_{OL}	Maximum Low-Level Output Voltage	$V_{in} = V_{IH}$ or V_{IL} $ I_{out} \leq 20 \mu\text{A}$	2.0	0.1	0.1	0.1	V
			4.5	0.1	0.1	0.1	
			6.0	0.1	0.1	0.1	
			$V_{in} = V_{IH}$ or V_{IL} $ I_{out} \leq 4.0 \text{ mA}$ $ I_{out} \leq 5.2 \text{ mA}$	4.5	0.26	0.33	
			6.0	0.26	0.33	0.40	
I_{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	± 0.1	± 1.0	± 1.0	μA
I_{CC}	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0 \mu\text{A}$	6.0	8	80	160	μA

NOTE: Information on typical parametric values can be found in Chapter 2.

AC ELECTRICAL CHARACTERISTICS ($C_L = 50$ pF, Input $t_r = t_f = 6$ ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			- 55 to 25°C	≤ 85°C	≤ 125°C	
f _{max}	Maximum Clock Frequency (50% Duty Cycle) (Figures 1 and 3)	2.0	5.4	4.4	3.6	MHz
		4.5	27	22	18	
		6.0	32	26	21	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q1 (Figures 1 and 3)	2.0	120	150	180	ns
		4.5	24	30	36	
		6.0	20	26	31	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q2 (Figures 1 and 3)	2.0	190	240	285	ns
		4.5	38	48	57	
		6.0	32	41	48	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q3 (Figures 1 and 3)	2.0	240	300	360	ns
		4.5	48	60	72	
		6.0	41	51	61	
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Clock to Q4 (Figures 1 and 3)	2.0	290	365	435	ns
		4.5	58	73	87	
		6.0	49	62	74	
t _{PHL}	Maximum Propagation Delay, Reset to any Q (Figures 2 and 3)	2.0	165	205	250	ns
		4.5	33	41	50	
		6.0	28	35	43	
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0	75	95	110	ns
		4.5	15	19	22	
		6.0	13	16	19	
C _{in}	Maximum Input Capacitance	—	10	10	10	pF

NOTES:

1. For propagation delays with loads other than 50 pF, see Chapter 2.
2. Information on typical parametric values can be found in Chapter 2.

CPD	Power Dissipation Capacitance (Per Counter)*	Typical @ 25°C, V _{CC} = 5.0 V		pF
		40		

* Used to determine the no-load dynamic power consumption: $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$. For load considerations, see Chapter 2.

TIMING REQUIREMENTS (Input $t_r = t_f = 6$ ns)

Symbol	Parameter	V _{CC} V	Guaranteed Limit			Unit
			- 55 to 25°C	≤ 85°C	≤ 125°C	
t _{rec}	Minimum Recovery Time, Reset Inactive to Clock (Figure 2)	2.0	50	65	75	ns
		4.5	10	13	15	
		6.0	9	11	13	
t _w	Minimum Pulse Width, Clock (Figure 1)	2.0	80	100	120	ns
		4.5	16	20	24	
		6.0	14	17	20	
t _w	Minimum Pulse Width, Reset (Figure 2)	2.0	125	155	190	ns
		4.5	25	31	38	
		6.0	21	26	32	
t _r , t _f	Maximum Input Rise and Fall Times (Figure 1)	2.0	1000	1000	1000	ns
		4.5	500	500	500	
		6.0	400	400	400	

NOTE: Information on typical parametric values can be found in Chapter 2.

PIN DESCRIPTIONS

INPUTS

Clock (Pins 1, 13)

Clock input. The internal flip-flops are toggled and the counter state advances on high-to-low transitions of the clock input.

CONTROL INPUTS

Reset (Pins 2, 12)

Active-high, asynchronous reset. A separate reset is pro-

vided for each counter. A high at the Reset input prevents counting and forces all four outputs low.

OUTPUTS

Q1, Q2, Q3, Q4 (Pins 3, 4, 5, 6, 8, 9, 10, 11)

Parallel binary outputs Q4 is the most significant bit.

SWITCHING WAVEFORMS

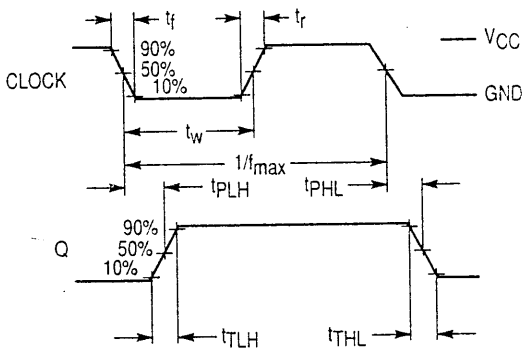


Figure 1.

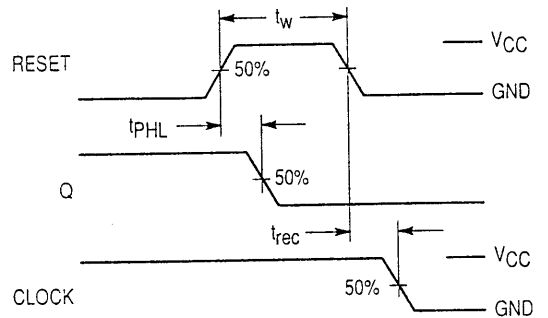
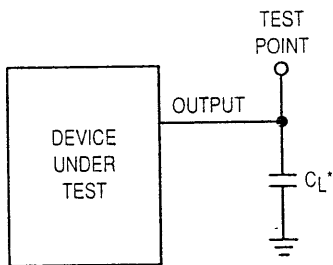


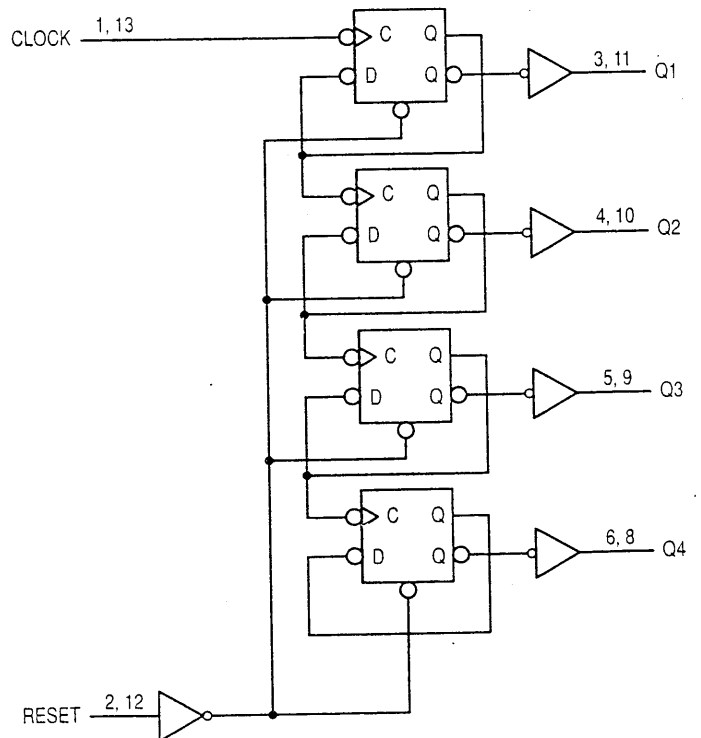
Figure 2.



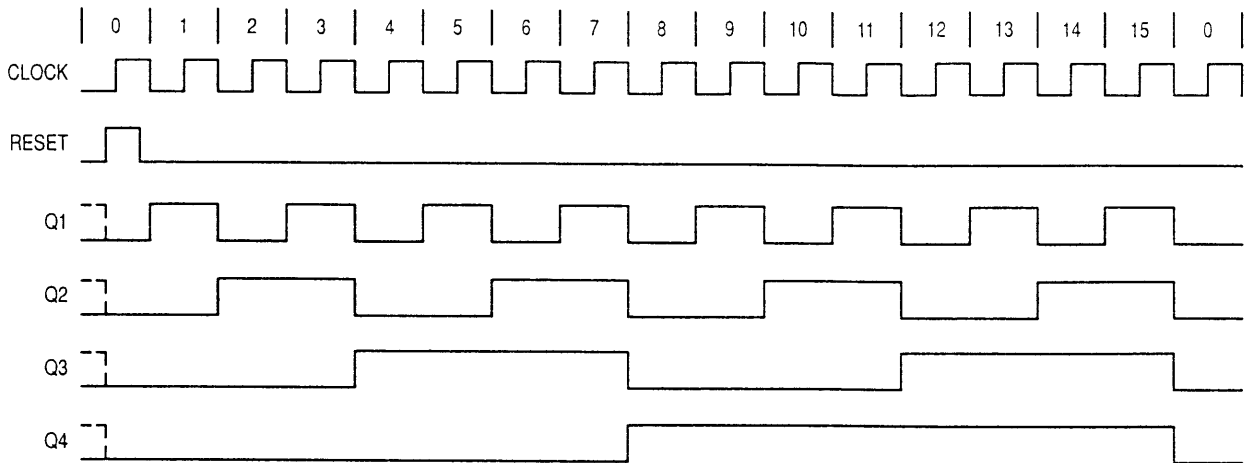
* Includes all probe and jig capacitance

Figure 3. Test Circuit

EXPANDED LOGIC DIAGRAM



TIMING DIAGRAM



COUNT SEQUENCE

Count	Outputs			
	Q4	Q3	Q2	Q1
0	L	L	L	L
1	L	L	L	H
2	L	L	H	L
3	L	L	H	H
4	L	H	L	L
5	L	H	L	H
6	L	H	H	L
7	L	H	H	H
8	H	L	L	L
9	H	L	L	H
10	H	L	H	L
11	H	L	H	H
12	H	H	L	L
13	H	H	L	H
14	H	H	H	L
15	H	H	H	H